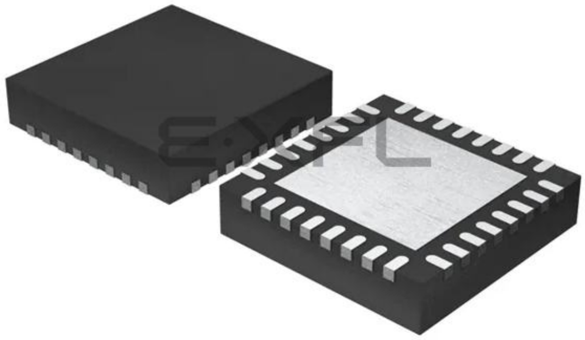

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, LINbus, SPI, TSI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, LVD, POR, PWM, WDT
Number of I/O	28
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 9x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount, Wettable Flank
Package / Case	32-VFQFN Exposed Pad
Supplier Device Package	32-HVQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl15z32vfm4r

1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to www.freescale.com and perform a part number search for the following device numbers: PKL15 and MKL15

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow • P = Prequalification
KL##	Kinetis family	• KL15
A	Key attribute	• Z = Cortex-M0+
FFF	Program flash memory size	• 32 = 32 KB • 64 = 64 KB • 128 = 128 KB • 256 = 256 KB

Table continues on the next page...

3.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior, which is guaranteed if you meet the accompanying operating requirements:

Symbol	Description	Min.	Max.	Unit
I_{WP}	Digital I/O weak pullup/ pulldown current	10	130	µA

3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

3.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

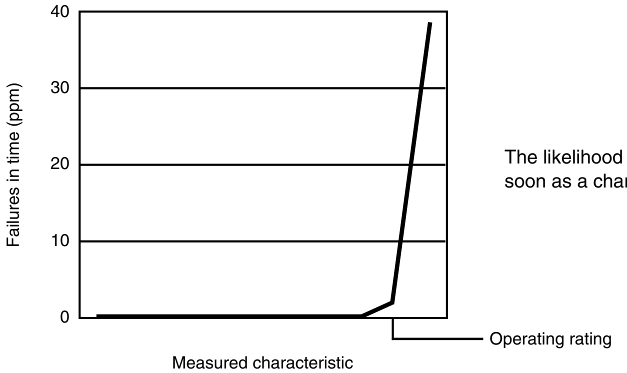
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

3.4.1 Example

This is an example of an operating rating:

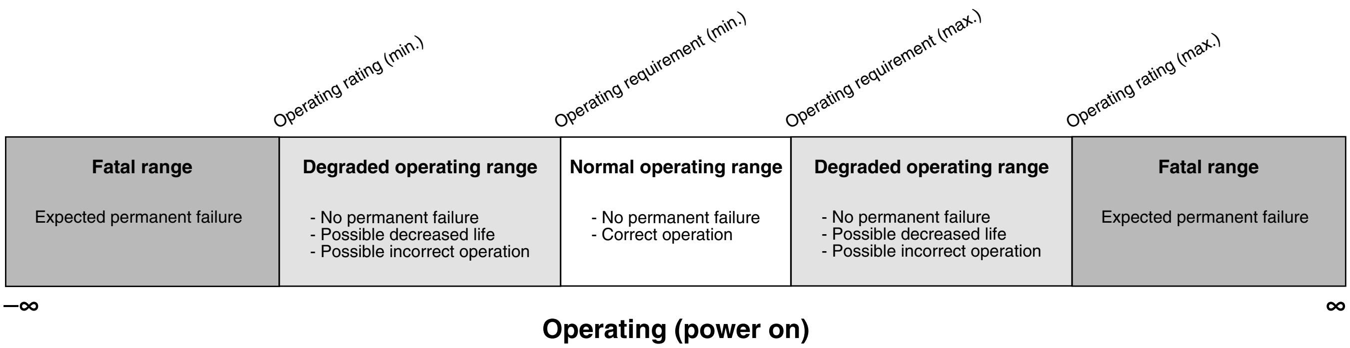
Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	–0.3	1.2	V

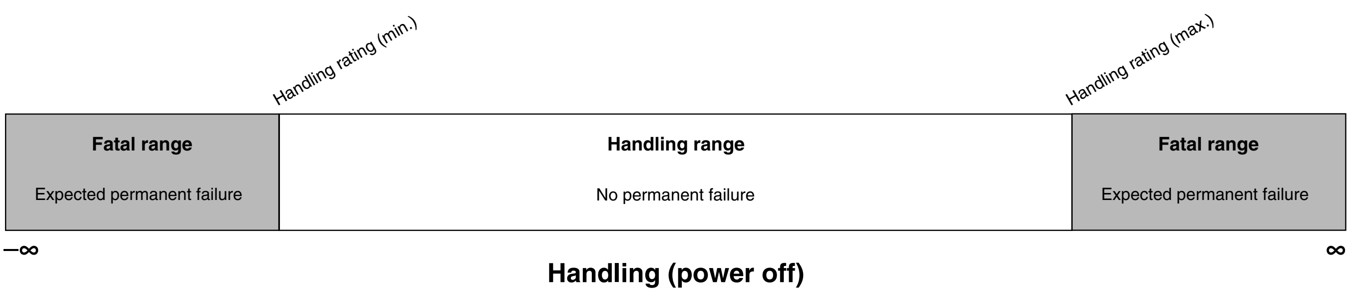
3.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

3.6 Relationship between ratings and operating requirements





3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	µA

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:

Table 1. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
I_{ICDIO}	Digital pin negative DC injection current — single pin • $V_{IN} < V_{SS}$-0.3V	-5	—	mA	1
I_{ICAIO}	Analog[2] pin DC injection current — single pin • $V_{IN} < V_{SS}$-0.3V (Negative current injection) • $V_{IN} > V_{DD}$+0.3V (Positive current injection)	-5 —	— +5	mA	3
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection • Positive current injection	-25 —	— +25	mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	

1. All digital I/O pins are internally clamped to V_{SS} through a ESD protection diode. There is no diode connection to V_{DD}. If V_{IN} greater than V_{DIO_MIN} (=V_{SS}-0.3V) is observed, then there is no need to provide current limiting resistors at the pads. If this limit cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{DIO\_MIN}-V_{IN})/|I_{IC}|$.
2. Analog pins are defined as pins that do not have an associated general purpose I/O port function.
3. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is greater than V_{AIO_MIN} (=V_{SS}-0.3V) and V_{IN} is less than V_{AIO_MAX}(=V_{DD}+0.3V) is observed, then there is no need to provide current limiting resistors at the pads. If these limits cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO\_MIN}-V_{IN})/|I_{IC}|$. The positive injection current limiting resistor is calcualted as $R=(V_{IN}-V_{AIO\_MAX})/|I_{IC}|$. Select the larger of these two calculated resistances.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±60	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	

Table continues on the next page...

5.2.5 Power consumption operating behaviors

Table 5. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
$I_{DD\_RUNCO\_CM}$	Run mode current in compute operation - 48 MHz core / 24 MHz flash/ bus disabled, LPTMR running using 4MHz internal reference clock, CoreMark® benchmark code executing from flash • at 3.0 V	—	6.4	—	mA	2
I_{DD_RUNCO}	Run mode current in compute operation - 48 MHz core / 24 MHz flash / bus clock disabled, code of while(1) loop executing from flash • at 3.0 V	—	4.1	5.2	mA	3
I_{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks disabled, code of while(1) loop executing from flash • at 3.0 V	—	5.1	6.3	mA	3
I_{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash • at 3.0 V • at 25 °C • at 125 °C	— —	6.4 6.8	7.8 8.3	mA mA	3, 4,
I_{DD_WAIT}	Wait mode current - core disabled / 48 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	—	3.7	5.0	mA	3
I_{DD_WAIT}	Wait mode current - core disabled / 24 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	—	2.9	4.2	mA	3
I_{DD_PSTOP2}	Stop mode current with partial stop 2 clocking option - core and system disabled / 10.5 MHz bus • at 3.0 V	—	2.5	3.7	mA	3
I_{DD_VLPRCO}	Very low power run mode current in compute operation - 4 MHz core / 0.8 MHz flash / bus clock disabled, code of while(1) loop executing from flash • at 3.0 V	—	188	570	µA	5
I_{DD_VLPR}	Very low power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks disabled, code of while(1) loop executing from flash • at 3.0 V	—	224	613	µA	5

Table continues on the next page...

Table 12. MCG specifications (continued)

Symbol	Description		Min.	Typ.	Max.	Unit	Notes
$f_{dco\_t\_DMX32}$	DCO output frequency	Low range (DRS = 00) 732 × f_{fll_ref}	—	23.99	—	MHz	5, 6
		Mid range (DRS = 01) 1464 × f_{fll_ref}	—	47.97	—	MHz	
J_{cyc_fll}	FLL period jitter • f_{VCO} = 48 MHz		—	180	—	ps	7
$t_{fll\_acquire}$	FLL target frequency acquisition time		—	—	1	ms	8
PLL							
f_{vco}	VCO operating frequency		48.0	—	100	MHz	
I_{pll}	PLL operating current • PLL at 96 MHz ($f_{osc\_hi\_1}$ = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 48)		—	1060	—	µA	9
I_{pll}	PLL operating current • PLL at 48 MHz ($f_{osc\_hi\_1}$ = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 24)		—	600	—	µA	9
f_{pll_ref}	PLL reference frequency range		2.0	—	4.0	MHz	
J_{cyc_pll}	PLL period jitter (RMS) • f_{vco} = 48 MHz • f_{vco} = 100 MHz		— —	120 50	— —	ps ps	10
J_{acc_pll}	PLL accumulated jitter over 1µs (RMS) • f_{vco} = 48 MHz • f_{vco} = 100 MHz		— —	1350 600	— —	ps ps	10
D_{lock}	Lock entry frequency tolerance		± 1.49	—	± 2.98	%	
D_{unl}	Lock exit frequency tolerance		± 4.47	—	± 5.97	%	
t_{pll_lock}	Lock detector detection time		—	—	$150 \times 10^{-6} + 1075(1/f_{pll\_ref})$	s	11

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. The deviation is relative to the factory trimmed frequency at nominal V_{DD} and 25 °C, f_{ints_ft}.
3. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 0.
4. The resulting system clock frequencies must not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco_t}) over voltage and temperature must be considered.
5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 1.
6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
7. This specification is based on standard deviation (RMS) of period or frequency.
8. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
9. Excludes any oscillator currents that are also consuming power while PLL is in operation.
10. This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
11. This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

Table 13. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
R_S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
V_{pp} [5]	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C_x,C_y can be provided by using the integrated capacitors when the low frequency oscillator (RANGE = 00) is used. For all other cases external capacitors must be used..
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

6.3.2.2 Oscillator frequency specifications

Table 14. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
$f_{osc\_hi\_1}$	Oscillator crystal or resonator frequency — high frequency mode (low range) (MCG_C2[RANGE]=01)	3	—	8	MHz	
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	48	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	

Table continues on the next page...

Table 14. Oscillator frequency specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.
2. When transitioning from FBE to FEI mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
3. Proper PC board layout procedures must be followed to achieve specifications.
4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

6.4 Memories and memory interfaces

6.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

6.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 15. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	μs	
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversall}$	Erase All high-voltage time	—	52	452	ms	1

1. Maximum time based on expectations at cycling end-of-life.

6.4.1.2 Flash timing specifications — commands

Table 16. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	μs	1
t_{pgmchk}	Program Check execution time	—	—	45	μs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	μs	1
t_{pgm4}	Program Longword execution time	—	65	145	μs	
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	
t_{rdonce}	Read Once execution time	—	—	25	μs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μs	
t_{ersall}	Erase All Blocks execution time	—	62	500	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1

1. Assumes 25MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

6.4.1.3 Flash high voltage current behaviors

Table 17. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.4.1.4 Reliability specifications

Table 18. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
			Program Flash			
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at -40°C ≤ T_j ≤ 125°C.

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

6.6 Analog

6.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in Table 19 and Table 20 are achievable on the differential pins ADCx_DP0, ADCx_DM0.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

6.6.1.1 16-bit ADC operating conditions

Table 19. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V_{DD} (V_{DD}-V_{DDA})	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} (V_{SS} - V_{SSA})	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	3
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	3
V_{ADIN}	Input voltage		V_{REFL}	—	V_{REFH}	V	
C_{ADIN}	Input capacitance	• 16-bit mode • 8-/10-/12-bit modes	— —	8 4	10 5	pF	
R_{ADIN}	Input resistance		—	2	5	kΩ	
R_{AS}	Analog source resistance	13-/12-bit modes f_{ADCK} < 4 MHz	—	—	5	kΩ	4
f_{ADCK}	ADC conversion clock frequency	≤ 1312-bit mode	1.0	—	18.0	MHz	5
f_{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	5
C_{rate}	ADC conversion rate	≤ 1312 bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	6

Table continues on the next page...

Table 20. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
E_{IL}	Input leakage error		$I_{In} \times R_{AS}$			mV	I_{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	—	1.715	—	mV/°C	
V_{TEMP25}	Temp sensor voltage	25 °C	—	719	—	mV	

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume V_{DDA} = 3.0 V, Temp = 25°C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and the ADLPC bit (low power). For lowest power operation the ADLPC bit must be set, the HSC bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.

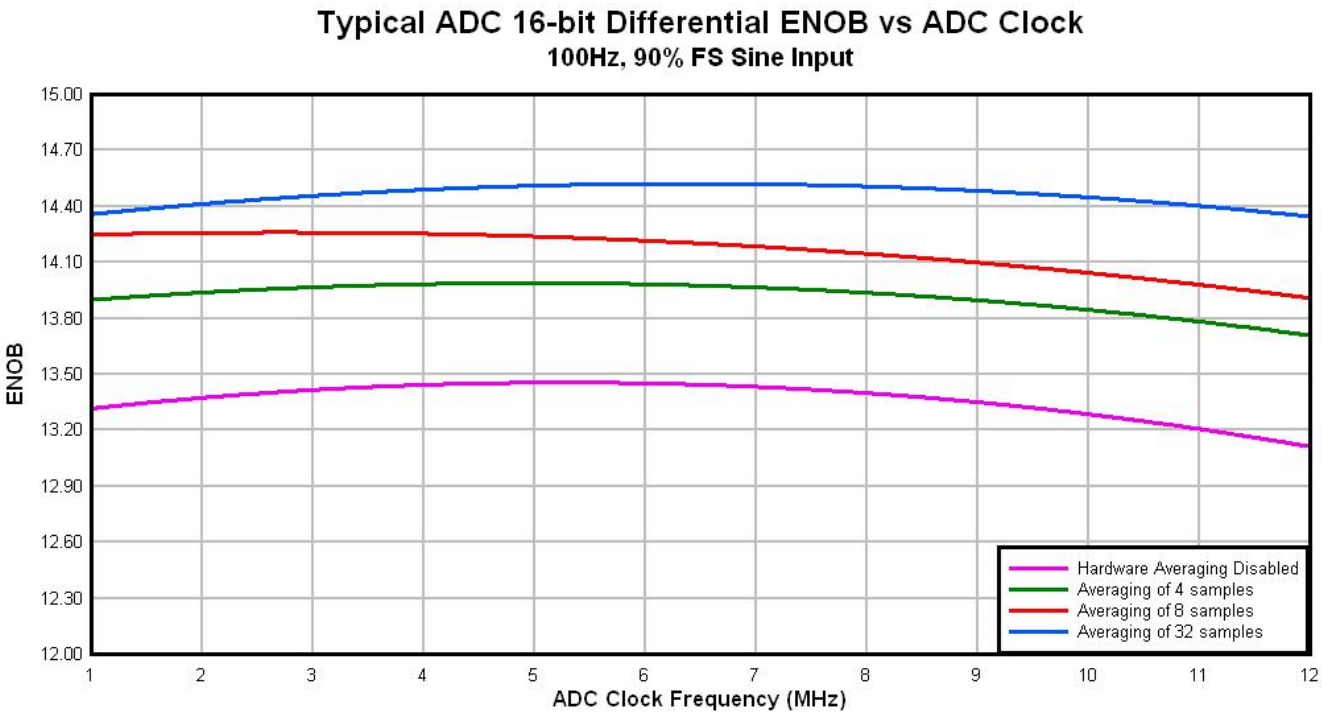


Figure 7. Typical ENOB vs. ADC_CLK for 16-bit differential mode

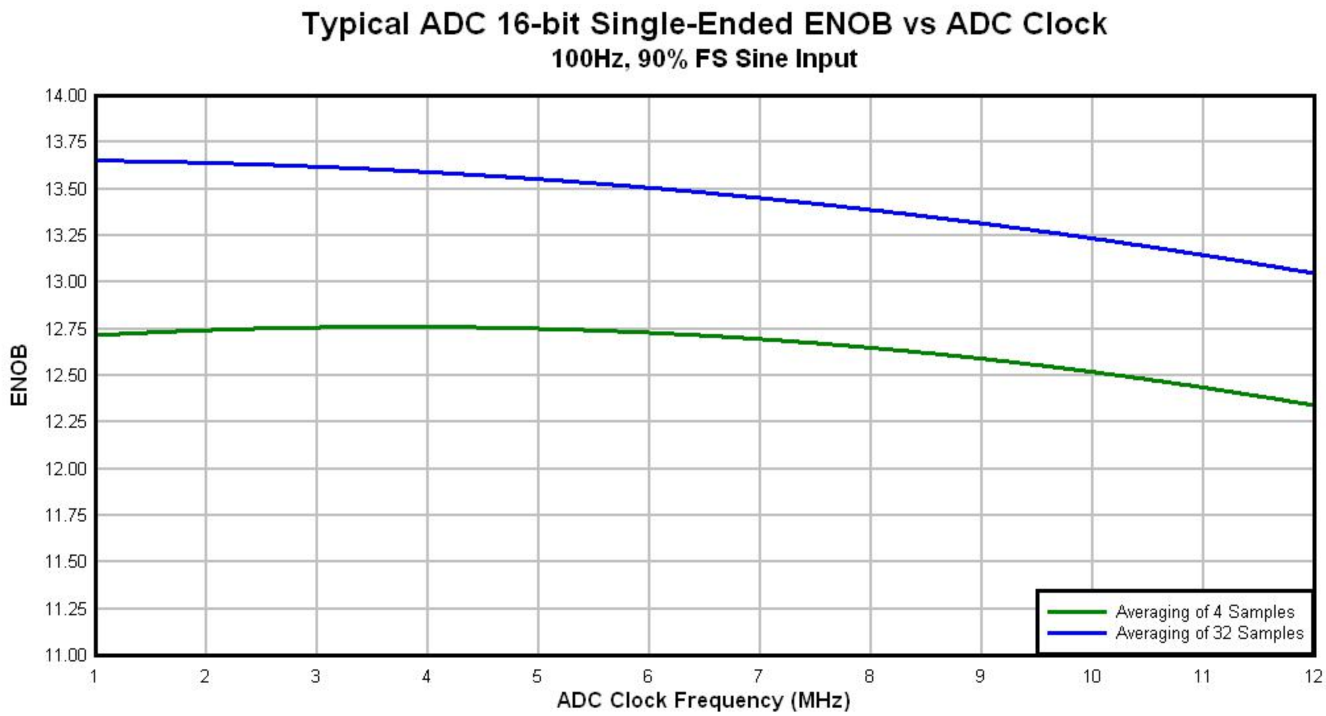


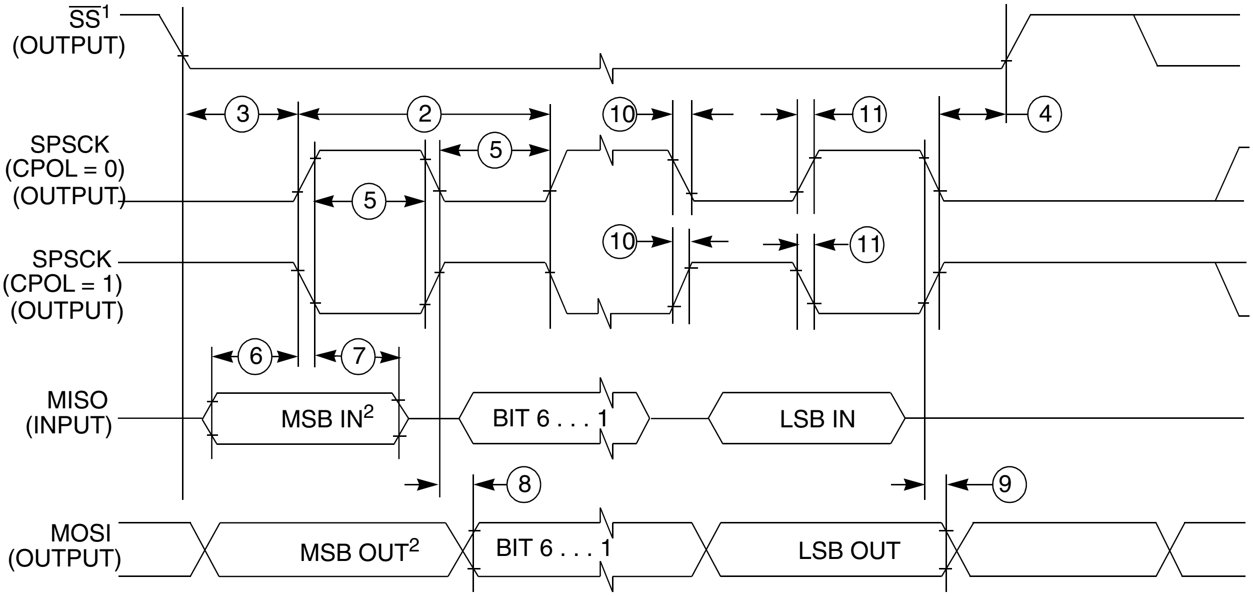
Figure 8. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

6.6.2 CMP and 6-bit DAC electrical specifications

Table 21. Comparator and 6-bit DAC electrical specifications

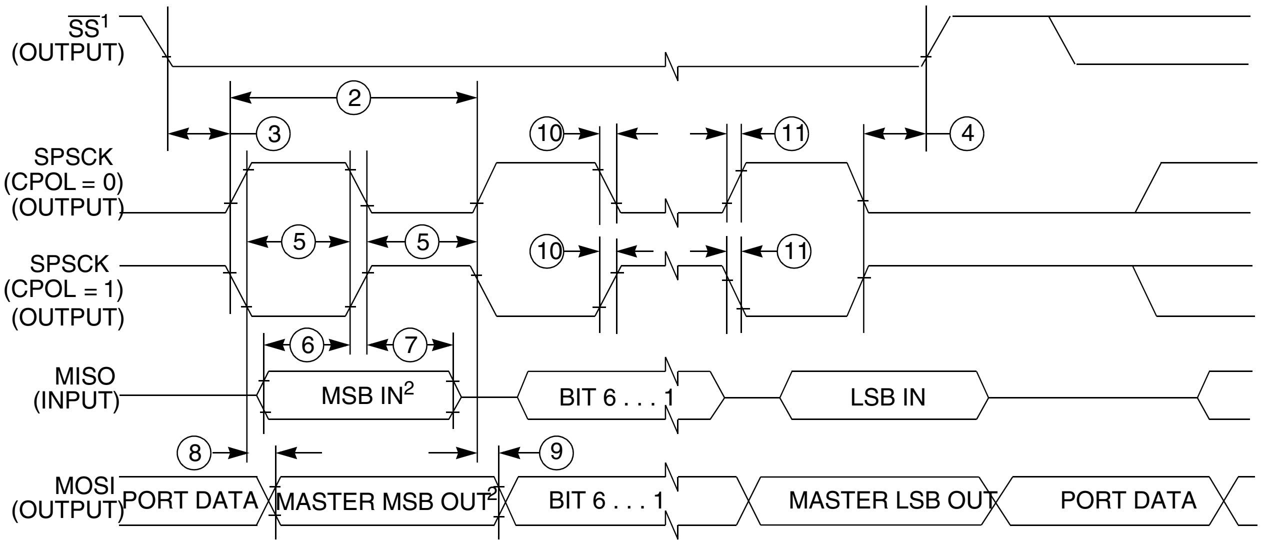
Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, high-speed mode (EN = 1, PMODE = 1)	—	—	200	μA
I_{DDLS}	Supply current, low-speed mode (EN = 1, PMODE = 0)	—	—	20	μA
V_{AIN}	Analog input voltage	V_{SS}	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis[1]				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOh}	Output high	V_{DD} – 0.5	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN = 1, PMODE = 1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN = 1, PMODE = 0)	80	250	600	ns

Table continues on the next page...



1. If configured as an output.
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 13. SPI master mode timing (CPHA = 0)



1.If configured as output
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 14. SPI master mode timing (CPHA = 1)

Table 26. SPI slave mode timing on slew rate disabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	t_{SPSCK}	SPSCK period	4 x t_{periph}	—	ns	2
3	t_{Lead}	Enable lead time	1	—	t_{periph}	—
4	t_{Lag}	Enable lag time	1	—	t_{periph}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} - 30	—	ns	—

Table continues on the next page...

8.1 KL15 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

80 LQFP	64 LQFP	48 QFN	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
1	1	—	1	PTE0	DISABLED		PTE0		UART1_TX	RTC_CLKOUT	CMP0_OUT	I2C1_SDA	
2	2	—	2	PTE1	DISABLED		PTE1	SPI1_MOSI	UART1_RX		SPI1_MISO	I2C1_SCL	
3	—	—	—	PTE2	DISABLED		PTE2	SPI1_SCK					
4	—	—	—	PTE3	DISABLED		PTE3	SPI1_MISO			SPI1_MOSI		
5	—	—	—	PTE4	DISABLED		PTE4	SPI1_PCS0					
6	—	—	—	PTE5	DISABLED		PTE5						
7	3	1	—	VDD	VDD	VDD							
8	4	2	—	VSS	VSS	VSS							
9	5	3	3	PTE16	ADC0_DP1/ ADC0_SE1	ADC0_DP1/ ADC0_SE1	PTE16	SPI0_PCS0	UART2_TX	TPM_CLKIN0			
10	6	4	4	PTE17	ADC0_DM1/ ADC0_SE5a	ADC0_DM1/ ADC0_SE5a	PTE17	SPI0_SCK	UART2_RX	TPM_CLKIN1		LPTMR0_ ALT3	
11	7	5	5	PTE18	ADC0_DP2/ ADC0_SE2	ADC0_DP2/ ADC0_SE2	PTE18	SPI0_MOSI		I2C0_SDA	SPI0_MISO		
12	8	6	6	PTE19	ADC0_DM2/ ADC0_SE6a	ADC0_DM2/ ADC0_SE6a	PTE19	SPI0_MISO		I2C0_SCL	SPI0_MOSI		
13	9	7	—	PTE20	ADC0_DP0/ ADC0_SE0	ADC0_DP0/ ADC0_SE0	PTE20		TPM1_CH0	UART0_TX			
14	10	8	—	PTE21	ADC0_DM0/ ADC0_SE4a	ADC0_DM0/ ADC0_SE4a	PTE21		TPM1_CH1	UART0_RX			
15	11	—	—	PTE22	ADC0_DP3/ ADC0_SE3	ADC0_DP3/ ADC0_SE3	PTE22		TPM2_CH0	UART2_TX			
16	12	—	—	PTE23	ADC0_DM3/ ADC0_SE7a	ADC0_DM3/ ADC0_SE7a	PTE23		TPM2_CH1	UART2_RX			
17	13	9	7	VDDA	VDDA	VDDA							
18	14	10	—	VREFH	VREFH	VREFH							
19	15	11	—	VREFL	VREFL	VREFL							
20	16	12	8	VSSA	VSSA	VSSA							
21	17	13	—	PTE29	CMP0_IN5/ ADC0_SE4b	CMP0_IN5/ ADC0_SE4b	PTE29		TPM0_CH2	TPM_CLKIN0			
22	18	14	9	PTE30	DAC0_OUT/ ADC0_SE23/ CMP0_IN4	DAC0_OUT/ ADC0_SE23/ CMP0_IN4	PTE30		TPM0_CH3	TPM_CLKIN1			
23	19	—	—	PTE31	DISABLED		PTE31		TPM0_CH4				
24	20	15	—	PTE24	DISABLED		PTE24		TPM0_CH0		I2C0_SCL		
25	21	16	—	PTE25	DISABLED		PTE25		TPM0_CH1		I2C0_SDA		
26	22	17	10	PTA0	SWD_CLK	TSI0_CH1	PTA0		TPM0_CH5				SWD_CLK
27	23	18	11	PTA1	DISABLED	TSI0_CH2	PTA1	UART0_RX	TPM2_CH0				
28	24	19	12	PTA2	DISABLED	TSI0_CH3	PTA2	UART0_TX	TPM2_CH1				

80 LQFP	64 LQFP	48 QFN	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
29	25	20	13	PTA3	SWD_DIO	TSI0_CH4	PTA3	I2C1_SCL	TPM0_CH0				SWD_DIO
30	26	21	14	PTA4	NMI_b	TSI0_CH5	PTA4	I2C1_SDA	TPM0_CH1				NMI_b
31	27	—	—	PTA5	DISABLED		PTA5		TPM0_CH2				
32	28	—	—	PTA12	DISABLED		PTA12		TPM1_CH0				
33	29	—	—	PTA13	DISABLED		PTA13		TPM1_CH1				
34	—	—	—	PTA14	DISABLED		PTA14	SPI0_PCS0	UART0_TX				
35	—	—	—	PTA15	DISABLED		PTA15	SPI0_SCK	UART0_RX				
36	—	—	—	PTA16	DISABLED		PTA16	SPI0_MOSI			SPI0_MISO		
37	—	—	—	PTA17	DISABLED		PTA17	SPI0_MISO			SPI0_MOSI		
38	30	22	15	VDD	VDD	VDD							
39	31	23	16	VSS	VSS	VSS							
40	32	24	17	PTA18	EXTAL0	EXTAL0	PTA18		UART1_RX	TPM_CLKIN0			
41	33	25	18	PTA19	XTAL0	XTAL0	PTA19		UART1_TX	TPM_CLKIN1		LPTMR0_ ALT1	
42	34	26	19	RESET_b	RESET_b		PTA20						
43	35	27	20	PTB0/ LLWU_P5	ADC0_SE8/ TSI0_CH0	ADC0_SE8/ TSI0_CH0	PTB0/ LLWU_P5	I2C0_SCL	TPM1_CH0				
44	36	28	21	PTB1	ADC0_SE9/ TSI0_CH6	ADC0_SE9/ TSI0_CH6	PTB1	I2C0_SDA	TPM1_CH1				
45	37	29	—	PTB2	ADC0_SE12/ TSI0_CH7	ADC0_SE12/ TSI0_CH7	PTB2	I2C0_SCL	TPM2_CH0				
46	38	30	—	PTB3	ADC0_SE13/ TSI0_CH8	ADC0_SE13/ TSI0_CH8	PTB3	I2C0_SDA	TPM2_CH1				
47	—	—	—	PTB8	DISABLED		PTB8		EXTRG_IN				
48	—	—	—	PTB9	DISABLED		PTB9						
49	—	—	—	PTB10	DISABLED		PTB10	SPI1_PCS0					
50	—	—	—	PTB11	DISABLED		PTB11	SPI1_SCK					
51	39	31	—	PTB16	TSI0_CH9	TSI0_CH9	PTB16	SPI1_MOSI	UART0_RX	TPM_CLKIN0	SPI1_MISO		
52	40	32	—	PTB17	TSI0_CH10	TSI0_CH10	PTB17	SPI1_MISO	UART0_TX	TPM_CLKIN1	SPI1_MOSI		
53	41	—	—	PTB18	TSI0_CH11	TSI0_CH11	PTB18		TPM2_CH0				
54	42	—	—	PTB19	TSI0_CH12	TSI0_CH12	PTB19		TPM2_CH1				
55	43	33	—	PTC0	ADC0_SE14/ TSI0_CH13	ADC0_SE14/ TSI0_CH13	PTC0		EXTRG_IN		CMP0_OUT		
56	44	34	22	PTC1/ LLWU_P6/ RTC_CLKIN	ADC0_SE15/ TSI0_CH14	ADC0_SE15/ TSI0_CH14	PTC1/ LLWU_P6/ RTC_CLKIN	I2C1_SCL		TPM0_CH0			
57	45	35	23	PTC2	ADC0_SE11/ TSI0_CH15	ADC0_SE11/ TSI0_CH15	PTC2	I2C1_SDA		TPM0_CH1			
58	46	36	24	PTC3/ LLWU_P7	DISABLED		PTC3/ LLWU_P7		UART1_RX	TPM0_CH2	CLKOUT		
59	47	—	—	VSS	VSS	VSS							
60	48	—	—	VDD	VDD	VDD							
61	49	37	25	PTC4/ LLWU_P8	DISABLED		PTC4/ LLWU_P8	SPI0_PCS0	UART1_TX	TPM0_CH3			

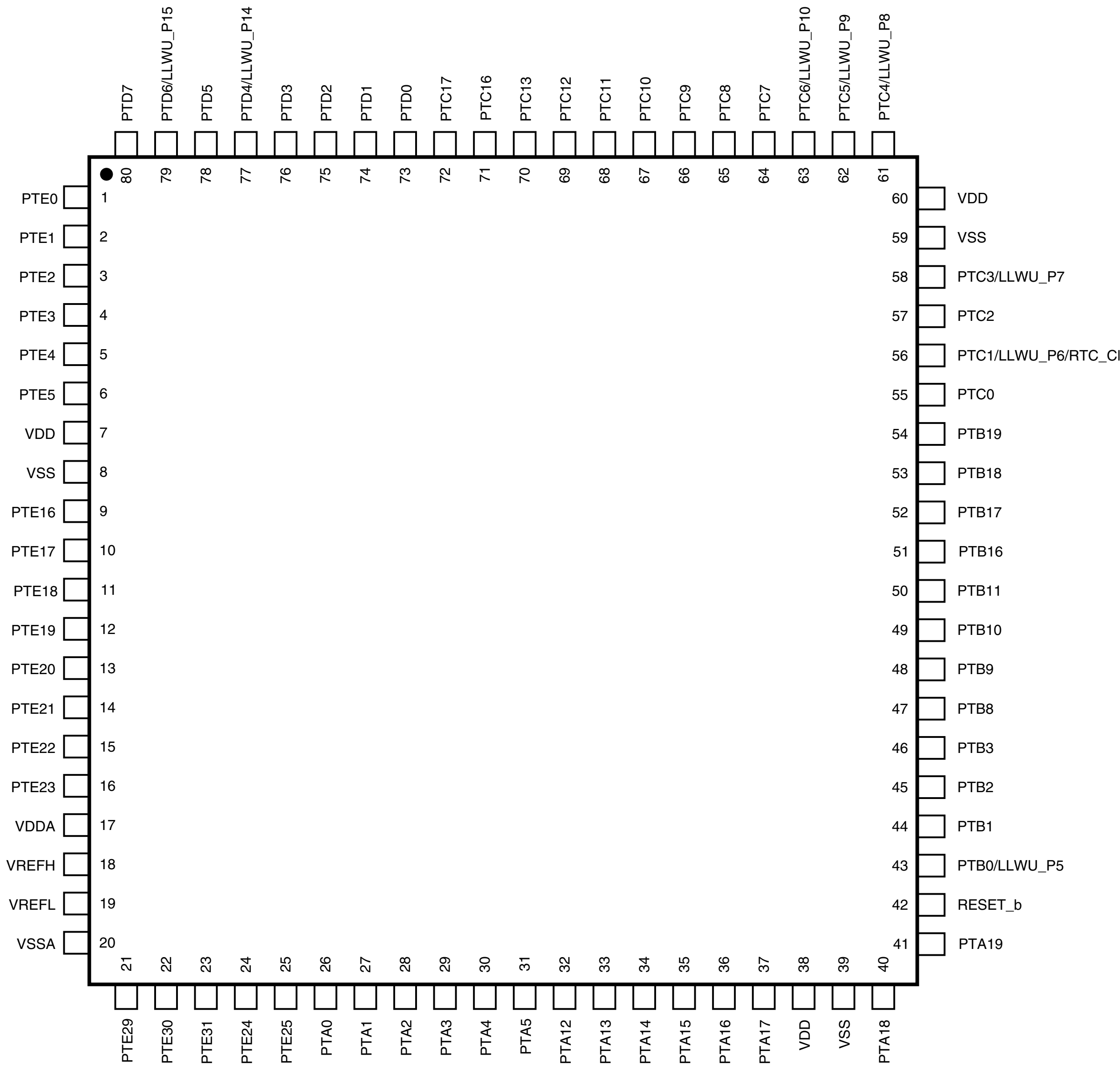


Figure 17. KL15 80-pin LQFP pinout diagram

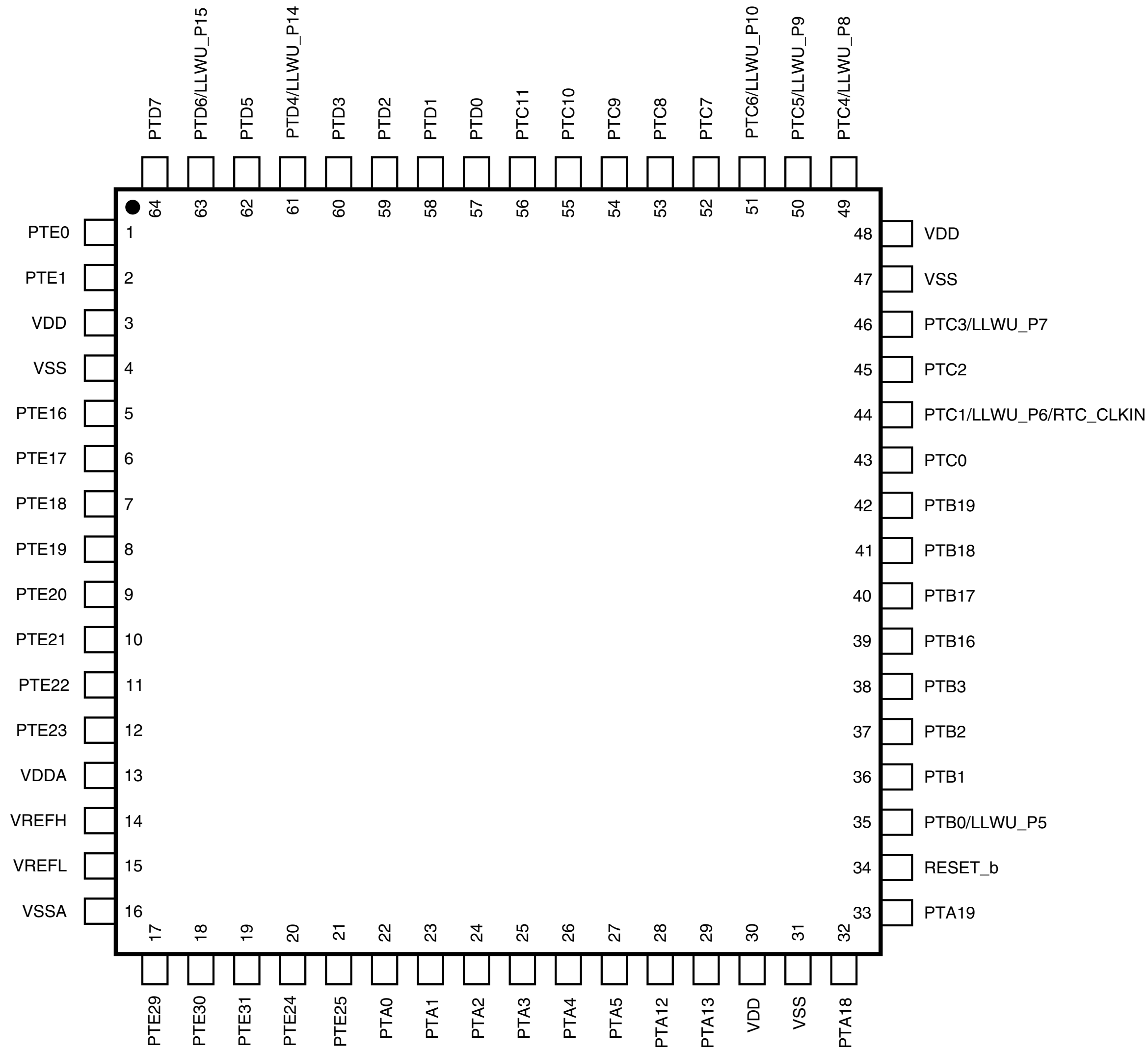


Figure 18. KL15 64-pin LQFP pinout diagram

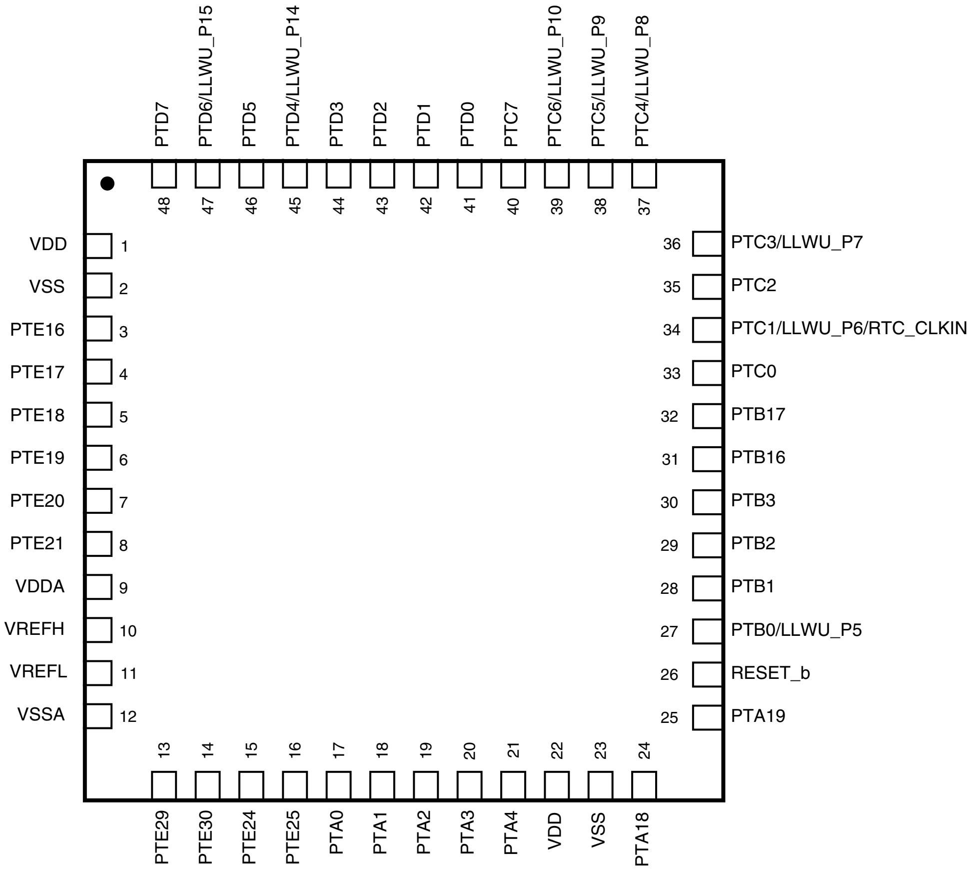


Figure 19. KL15 48-pin QFN pinout diagram

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